IDS 12/12/2003

Form PTO-1449 - U.S. DEPARTMENT OF COMMERCE (REV. 7-80)PATENT AND TRADEMARK OFFICE LIST OF PRIOR ART CITED BY APPLICANT (Use several sheets if necessary)					ly. Docket No. DR919970121US2 (1	Serial N . 19/735, 167				
					Applicant Frank Cardone, et al.					
					ing Date erewith	Group 2822				
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EXAMINER										

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.